

MOS INTEGRATED CIRCUIT μPD43256B-X

256K-BIT CMOS STATIC RAM 32K-WORD BY 8-BIT EXTENDED TEMPERATURE OPERATION

Description

The μ PD43256B-X is a high speed, low power, and 262,144 bits (32,768 words by 8 bits) CMOS static RAM.

The μ PD43256B-X is an extended-operating-temperature version of the μ PD43256B (X version : T_A = -25 to +85°C).

And A and B versions are low voltage operations. Battery backup is available.

The μPD43256B-X is packed in 28-pin PLASTIC TSOP (I) (8 x 13.4 mm).

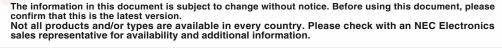
Features

- 32,768 words by 8 bits organization
- Fast access time: 70, 85, 100, 120, 150 ns (MAX.)
- Operating ambient temperature: T_A = −25 to +85 °C
- Low voltage operation (A version: Vcc = 3.0 to 5.5 V, B version: Vcc = 2.7 to 5.5 V)
- Low Vcc data retention: 2.0 V (MIN.)
- /OE input for easy application

TOE Input for easy c									
Part number	Access time	Operating supply	Operating ambient	Supply current					
	ns (MAX.)	voltage	temperature	At operating	At standby	At data retention			
W.		V	°C	mA (MAX.)	μΑ (MAX.)	μΑ (MAX.) Note1			
μPD43256B-xxX	70, 85	4.5 to 5.5	-25 to +85	45	50	2			
μPD43256B-AxxX	85 Note2, 100, 120 Note2	3.0 to 5.5		A 15-	ZUW.DZ	50.0			
μPD43256B-BxxX Note2	100, 120 Note2, 150 Note2	2.7 to 5.5	4	40	All As				

Notes 1. Ta \leq 40 °C, Vcc = 3.0 V

2. 100 ns (MAX.) (Vcc = 4.5 to 5.5 V)







Ordering Information

Part number	Package	Access time	Operating supply	Operating ambient	Remark
		ns (MAX.)	voltage	temperature	
			V	°C	
μPD43256BGW-70X-9JL	28-pin PLASTIC TSOP(I)	70	4.5 to 5.5	-25 to +85	
μPD43256BGW-85X-9JL	(8x13.4) (Normal bent)	85			
μPD43256BGW-A85X-9JL		85	3.0 to 5.5		A version
μPD43256BGW-A10X-9JL		100			
μPD43256BGW-A12X-9JL		120			
μPD43256BGW-B10X-9JL		100	2.7 to 5.5		B version
μPD43256BGW-B12X-9JL		120			
μPD43256BGW-B15X-9JL		150			
μPD43256BGW-70X-9KL	28-pin PLASTIC TSOP(I)	70	4.5 to 5.5		
μPD43256BGW-85X-9KL	(8x13.4) (Reverse bent)	85			
μPD43256BGW-A85X-9KL		85	3.0 to 5.5		A version
μPD43256BGW-A10X-9KL		100			
μPD43256BGW-A12X-9KL		120			
μPD43256BGW-B10X-9KL		100	2.7 to 5.5		B version
μPD43256BGW-B12X-9KL		120			
μPD43256BGW-B15X-9KL		150			
μPD43256BGW-70X-9JL-A	28-pin PLASTIC TSOP(I)	70	4.5 to 5.5		
μPD43256BGW-85X-9JL-A	(8x13.4) (Normal bent)	85			
μPD43256BGW-A85X-9JL-A		85	3.0 to 5.5		A version
μPD43256BGW-A10X-9JL-A		100			
μPD43256BGW-A12X-9JL-A		120			
μPD43256BGW-B10X-9JL-A		100	2.7 to 5.5		B version
μPD43256BGW-B12X-9JL-A		120			
μPD43256BGW-B15X-9JL-A		150			
μPD43256BGW-70X-9KL-A	28-pin PLASTIC TSOP(I)	70	4.5 to 5.5		
μPD43256BGW-85X-9KL-A	(8x13.4) (Reverse bent)	85			
μPD43256BGW-A85X-9KL-A		85	3.0 to 5.5		A version
μPD43256BGW-A10X-9KL-A		100			
μPD43256BGW-A12X-9KL-A		120			
μPD43256BGW-B10X-9KL-A		100	2.7 to 5.5		B version
μPD43256BGW-B12X-9KL-A		120			
μPD43256BGW-B15X-9KL-A		150			

Remark Products with -A at the end of the part number are lead-free products.

Pin Configurations (Marking Side)

/xxx indicates active low signal.

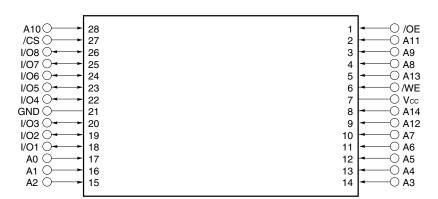
28-pin PLASTIC TSOP(I) (8x13.4) (Normal bent)

[μPD43256BGW-xxX-9JL]
[μPD43256BGW-AxxX-9JL]
[μPD43256BGW-BxxX-9JL]
[μPD43256BGW-xxX-9JL-A]
[μPD43256BGW-AxxX-9JL-A]
[μPD43256BGW-BxxX-9JL-A]



28-pin PLASTIC TSOP(I) (8x13.4) (Reverse bent)

[μPD43256BGW-xxX-9KL]
[μPD43256BGW-AxxX-9KL]
[μPD43256BGW-BxXX-9KL]
[μPD43256BGW-xxX-9KL-A]
[μPD43256BGW-AxxX-9KL-A]
[μPD43256BGW-BxxX-9KL-A]

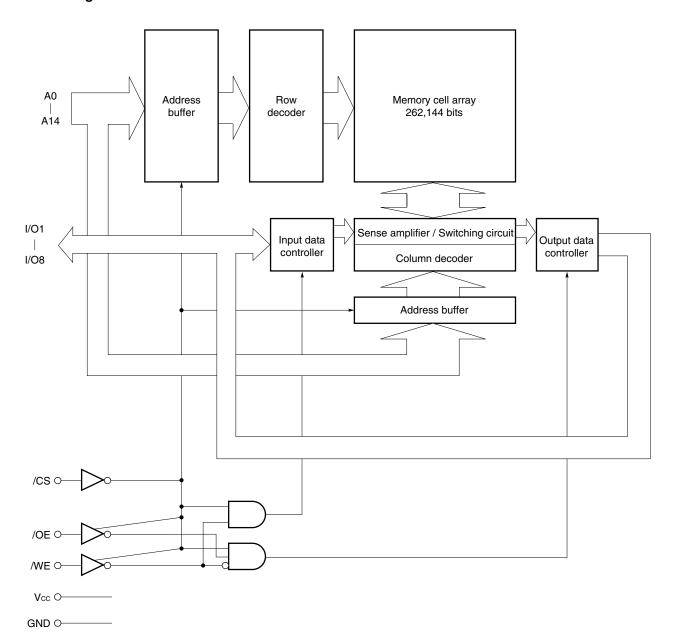


A0 - A14 : Address inputs /OE : Output Enable I/O1 - I/O8 : Data inputs / outputs Vcc : Power supply /CS : Chip Select GND : Ground

/WE : Write Enable

Remark Refer to Package Drawings for the 1-pin index mark.

Block Diagram



Truth Table

/CS	/OE	/WE	Mode	I/O	Supply current
Н	×	×	Not selected	High impedance	IsB
L	Н	Н	Output disable		ICCA
L	×	L	Write	Din	
L	L	Н	Read	D оит	

Remark ×: VIH or VIL



Electrical Specifications

Absolute Maximum Ratings

Parameter	Symbol	Condition	Rating	Unit
Supply voltage	Vcc		-0.5 Note to +7.0	٧
Input / Output voltage	VT		-0.5 Note to Vcc + 0.5	V
Operating ambient temperature	TA		-25 to +85	°C
Storage temperature	Tstg		-55 to +125	°C

Note -3.0 V (MIN.) (Pulse width: 50 ns)

Caution Exposing the device to stress above those listed in Absolute Maximum Rating could cause permanent damage. The device is not meant to be operated under conditions outside the limits described in the operational section of this specification. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability.

Recommended Operating Conditions

Parameter	Symbol	Condition	μPD43256B-xxX		μPD43256B-AxxX		μPD4325	Unit	
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Supply voltage	Vcc		4.5	5.5	3.0	5.5	2.7	5.5	٧
High level input voltage	VIH		2.4	Vcc+0.5	2.4	Vcc+0.5	2.4	Vcc+0.5	٧
Low level input voltage	VıL		-0.3 Note	+0.6	-0.3 Note	+0.4	-0.3 Note	+0.4	٧
Operating ambient temperature	Та		-25	+85	-25	+85	-25	+85	°C

Note -3.0 V (MIN.) (Pulse width: 50 ns)

Capacitance ($T_A = 25^{\circ}C$, f = 1 MHz)

Parameter	Symbol	Test conditions	MIN.	TYP.	MAX.	Unit
Input capacitance	Cin	Vin = 0 V			5	pF
Input / Output capacitance	C _{I/O}	V ₁ /O = 0 V			8	pF

Remarks 1. VIN: Input voltage

V_{I/O}: Input / Output voltage

2. These parameters are periodically sampled and not 100% tested.

Data Sheet M11012EJ6V0DS

DC Characteristics (Recommended Operating Conditions Unless Otherwise Noted) (1/2)

Parameter	Symbol	Test condition	μΡΙ	D43256B-	xxX	Unit
			MIN.	TYP.	MAX.	
Input leakage current	lц	V _{IN} = 0 V to V _{CC}	-1.0		+1.0	μΑ
I/O leakage current	ILO	V _{I/O} = 0 V to V _{CC} , /OE = V _{IH} or	-1.0		+1.0	μΑ
		/CS = VIH or /WE = VIL				
Operating supply current	ICCA1	/CS = V _{IL} , Minimum cycle time, I _{VO} = 0 mA			45	mA
	ICCA2	/CS = V _{IL} , I _{I/O} = 0 mA			15	
	Іссаз	/CS ≤ 0.2 V, Cycle = 1 MHz,			15	
		$I_{VO} = 0$ mA, $V_{IL} \le 0.2$ V, $V_{IH} \ge V_{CC} - 0.2$ V				
Standby supply current	IsB	/CS = V _{IH}			3	mA
	I _{SB1}	/CS ≥ Vcc - 0.2 V		1.0	50	μА
High level output voltage	V _{OH1}	Іон = -1.0 mA	2.4			V
	V _{OH2}	Іон = -0.1 mA	Vcc-0.5			
Low level output voltage	Vol	IoL = 2.1 mA			0.4	V

Remarks 1. VIN: Input voltage

V_{I/O}: Input / Output voltage

2. These DC characteristics are in common regardless of package types.

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DC Characteristics (Recommended Operating Conditions Unless Otherwise Noted) (2/2)

Parameter	Symbol	Test condition			μPD	43256B-	AxxX	μPD	43256B-	BxxX	Unit
						TYP.	MAX.	MIN.	TYP.	MAX.	
Input leakage current	lu	V _{IN} = 0 V to V _{CC}					+1.0	-1.0		+1.0	μΑ
I/O leakage current	ILO	$V_{I/O} = 0 \text{ V to Vcc, /OE}$	= VIH or		-1.0		+1.0	-1.0		+1.0	μΑ
		/CS = VIH or /WE = VI	L								
Operating supply current	ICCA1	/CS = VIL,	μPD43	256B-A85X			45			_	mA
		Minimum cycle time,	μPD43	256B-A10X			40			_	
		I _{1/O} = 0 mA	μPD43	256B-A12X			40			_	
			μPD43	256B-B10X			_			40	
			μPD43	256B-B12X			-			40	
			μPD43	256B-B15X			-			40	
				Vcc ≤ 3.3 V			-			25	
	ICCA2	/CS = VIL, II/O = 0 mA	5 = V _{IL} , I _{I/O} = 0 mA				15			15	
				Vcc ≤ 3.3 V			-			10	
	Іссаз	/CS ≤ 0.2 V, Cycle =	1 MHz, li	/o = 0 mA,			15			15	
		$V_{\text{IL}} \leq 0.2 \text{ V}, \text{ V}_{\text{IH}} \geq V_{\text{CC}}$	– 0.2 V	Vcc ≤ 3.3 V			_			10	
Standby supply current	IsB	/CS = ViH					3			3	mA
				Vcc ≤ 3.3 V			_			2	
	I _{SB1}	/CS ≥ Vcc - 0.2 V				1.0	50		1.0	50	μΑ
				Vcc ≤ 3.3 V			_			25	
High level output voltage	V _{OH1}	Iон = −1.0 mA, Vcc ≥ 4	4.5 V		2.4			2.4			V
		Іон = -0.5 mA, Vcc < 4.5 V			2.4			2.4			
	V _{OH2}	lон = −0.02 mA		Vcc-			Vcc-				
				0.1			0.1				
Low level output voltage	Vol	IoL = 2.1 mA, Vcc ≥ 4.5 V					0.4			0.4	٧
		IoL = 1.0 mA, Vcc < 4.	5 V				0.4			0.4	
	V _{OL1}	IoL = 0.02 mA					0.1			0.1	

Remarks 1. VIN: Input voltage

Vi/o: Input / Output voltage

2. These DC characteristics are in common regardless of package types.

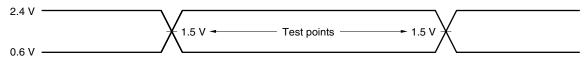
Data Sheet M11012EJ6V0DS

AC Characteristics (Recommended Operating Conditions Unless Otherwise Noted)

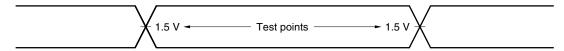
AC Test Conditions

$[\mu PD43256B-70X, \mu PD43256B-85X]$

Input Waveform (Rise and Fall Time ≤ 5 ns)

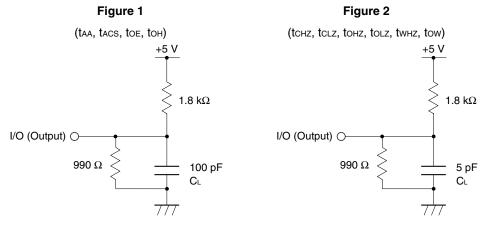


Output Waveform



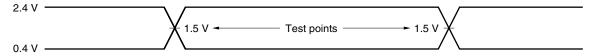
Output Load

AC characteristics should be measured with the following output load conditions.

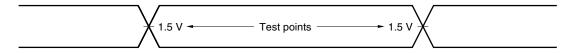


Remark C_L includes capacitance of the probe and jig, and stray capacitance.

[μ PD43256B-A85X, μ PD43256B-A10X, μ PD43256B-A12X, μ PD43256B-B10X, μ PD43256B-B12X, μ PD43256B-B15X] Input Waveform (Rise and Fall Time \leq 5 ns)



Output Waveform



Output Load

AC characteristics should be measured with the following output load conditions.

taa, tacs, toe, toh	tcнz, tcLz, tонz, toLz, twнz, tow
1TTL + 50 pF	1TTL + 5 pF



Read Cycle (1/2)

Parameter	Symbol		Vcc ≥ 4.5 V							
		μPD43256B-70X		μPD43256B-85X		μPD43256B-AxxX			dition	
						μPD4325	6B-BxxX			
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.			
Read cycle time	t RC	70		85		100		ns		
Address access time	taa		70		85		100	ns	Note	
/CS access time	tacs		70		85		100	ns		
/OE access time	toe		35		40		50	ns		
Output hold from address change	tон	10		10		10		ns		
/CS to output in low impedance	tclz	10		10		10		ns		
/OE to output in low impedance	tolz	5		5		5		ns		
/CS to output in high impedance	tснz		30		30		35	ns		
/OE to output in high impedance	tонz		30		30		35	ns		

Note See the output load.

Remark These AC characteristics are in common regardless of package types and L, LL versions.

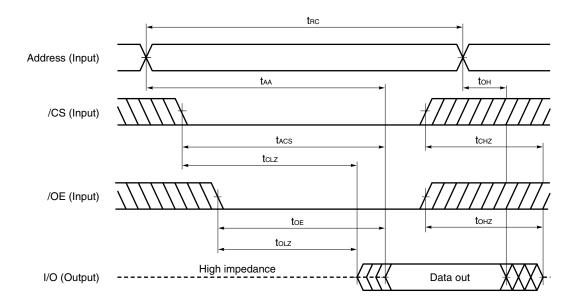
Read Cycle (2/2)

Parameter	Symbol	Vcc ≥ 3.0 V				Vcc ≥ 2.7 V							Unit	Con-	
			μPD43256B- μPD43256 A85X A10X			6B- μPD43256B- A12X			3256B- 0X	l '	3256B- 2X	μPD43256B- B15X			dition
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
Read cycle time	t RC	85		100		120		100		120		150		ns	
Address access time	taa		85		100		120		100		120		150	ns	Note
/CS access time	tacs		85		100		120		100		120		150	ns	
/OE access time	toe		50		60		60		60		60		70	ns	
Output hold from address change	tон	10		10		10		10		10		10		ns	
/CS to output in low impedance	tclz	10		10		10		10		10		10		ns	
/OE to output in low impedance	torz	5		5		5		5		5		5		ns	
/CS to output in high impedance	tснz		35		35		40		35		40		50	ns	
/OE to output in high impedance	tонz		35		35		40		35		40		50	ns	

Note See the output load.

Remark These AC characteristics are in common regardless of package types.

Read Cycle Timing Chart



 $\textbf{Remark} \quad \text{ In read cycle, /WE should be fixed to high level.}$



Write Cycle (1/2)

Parameter	Symbol			Vcc	≥ 4.5 V			Unit	Con-
		μPD432	μPD43256B-70X		μPD43256B-85X		μPD43256B-AxxX		dition
			· · · · · · · · · · · · · · · · · · ·			μPD4325	6B-BxxX		
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
Write cycle time	twc	70		85		100		ns	
/CS to end of write	tcw	60		70		80		ns	
Address valid to end of write	taw	60		70		80		ns	
Write pulse width	twp	55		60		70		ns	
Data valid to end of write	tow	30		35		40		ns	
Data hold time	tон	5		5		5		ns	
Address setup time	tas	0		0		0		ns	
Write recovery time	twr	0		0		0		ns	
/WE to output in high impedance	twнz		30	·	30		35	ns	Note
Output active from end of write	tow	5		5		5		ns	

Note See the output load.

Remark These AC characteristics are in common regardless of package types and L, LL versions.

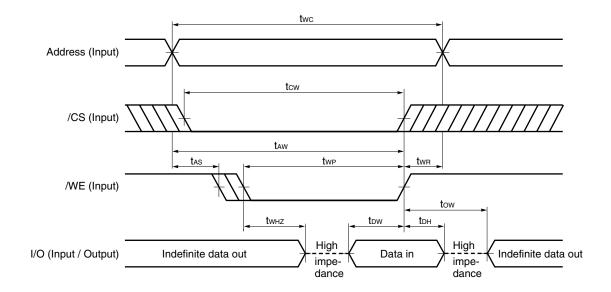
Write Cycle (2/2)

Parameter	Symbol	Vcc			Vcc ≥ 3.0 V			Vcc ≥ 2.7 V					Unit	Con-	
		μPD43	3256B-	μPD43	3256B-	μPD43	3256B-	μPD43	3256B-	μPD43	3256B-	μPD43	3256B-		dition
		A8	5X	A1	0X	A1	2X	B1	0X	B1	2X	B1	5X		
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
Write cycle time	twc	85		100		120		100		120		150		ns	
/CS to end of write	tcw	70		70		90		70		90		100		ns	
Address valid to	taw	70		70		90		70		90		100		ns	
end of write															
Write pulse width	twp	60		60		80		60		80		90		ns	
Data valid to end	tow	60		60		70		60		70		80		ns	
of write															
Data hold time	tон	5		5		5		5		5		5		ns	
Address setup time	tas	0		0		0		0		0		0		ns	
Write recovery time	twn	0		0		0		0		0		0		ns	
/WE to output in	twнz		35		35		40		35		40		40	ns	Note
high impedance															
Output active	tow	5		5		5		5		5		5		ns	
from end of write															

Note See the output load.

Remark These AC characteristics are in common regardless of package types.

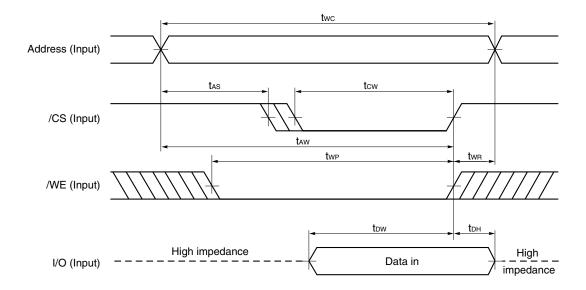
Write Cycle Timing Chart 1 (/WE Controlled)



Cautions 1. /CS or /WE should be fixed to high level during address transition.

- 2. When I/O pins are in the output state, do not apply to the I/O pins signals that are opposite in phase with output signals.
- Remarks 1. Write operation is done during the overlap time of a low level /CS and a low level /WE.
 - 2. When /WE is at low level, the I/O pins are always high impedance. When /WE is at high level, read operation is executed. Therefore /OE should be at high level to make the I/O pins high impedance.
 - 3. If /CS changes to low level at the same time or after the change of /WE to low level, the I/O pins will remain high impedance state.

Write Cycle Timing Chart 2 (/CS Controlled)



Cautions 1. /CS or /WE should be fixed to high level during address transition.

2. When I/O pins are in the output state, do not apply to the I/O pins signals that are opposite in phase with output signals.

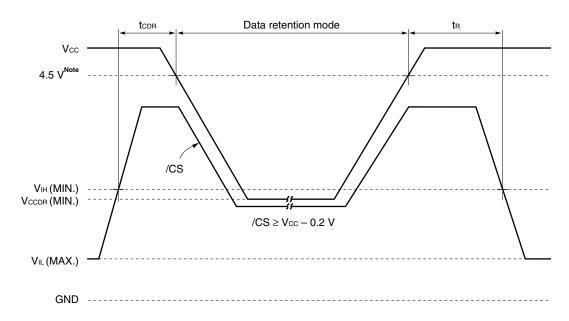
Remark Write operation is done during the overlap time of a low level /CS and a low level /WE.

Low Vcc Data Retention Characteristics ($T_A = -25 \text{ to } +85 \text{ }^{\circ}\text{C}$)

Parameter	Symbol	Test Condition	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	Vccdr	/CS ≥ Vcc - 0.2 V	2.0		5.5	V
Data retention supply current	Iccdr	Vcc = 3.0 V, /CS ≥ Vcc – 0.2 V		0.5	20 Note	μΑ
Chip deselection to data retention mode	tcdr		0			ns
Operation recovery time	t⊓		5			ms

Note $2 \mu A (T_A \le 40 \, ^{\circ}C), 7 \mu A (T_A \le 70 \, ^{\circ}C)$

Data Retention Timing Chart



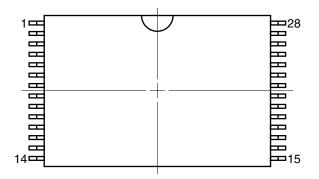
Note A version: 3.0 V, B version: 2.7 V

Remark The other pins (Address, /OE, /WE, I/O) can be in high impedance state.

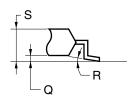
14

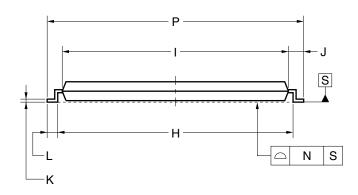
Package Drawings

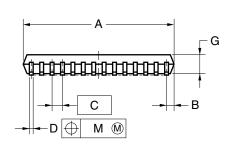
28-PIN PLASTIC TSOP(I) (8x13.4)



detail of lead end







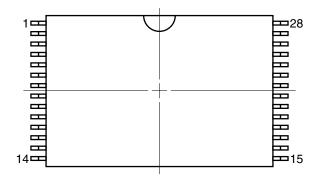
NOTES

- Each lead centerline is located within 0.08 mm of its true position (T.P.) at maximum material condition.
- 2. "A" excludes mold flash. (Includes mold flash: 8.4mm MAX.)

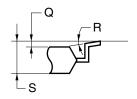
ITEM	MILLIMETERS			
Α	8.0±0.1			
В	0.6 MAX.			
С	0.55 (T.P.)			
D	$0.22^{+0.08}_{-0.07}$			
G	1.0			
Н	12.4±0.2			
	11.8±0.1			
J	0.8±0.2			
K	$0.145^{+0.025}_{-0.015}$			
L	0.5±0.1			
М	0.08			
N	0.10			
Р	13.4±0.2			
Q	0.1±0.05			
R	3°+7° -3°			
S	1.2 MAX.			

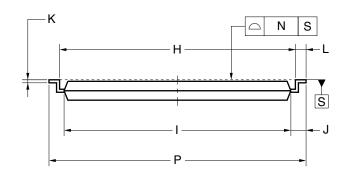
P28GW-55-9JL-2

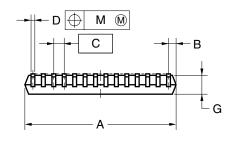
28-PIN PLASTIC TSOP(I) (8x13.4)



detail of lead end







NOTE

- 1. Each lead centerline is located within 0.08 mm of its true position (T.P.) at maximum material condition.
- 2. "A" excludes mold flash. (Includes mold flash: 8.4mm MAX.)

ITEM	MILLIMETERS		
Α	8.0±0.1		
В	0.6 MAX.		
С	0.55 (T.P.)		
D	$0.22^{+0.08}_{-0.07}$		
G	1.0		
Н	12.4±0.2		
ı	11.8±0.1		
J	0.8±0.2		
К	$0.145^{+0.025}_{-0.015}$		
L	0.5±0.1		
М	0.08		
N	0.10		
Р	13.4±0.2		
Q	0.1±0.05		
R	3°+7° -3°		
S	1.2 MAX.		
	DOOCW EE OKL O		

P28GW-55-9KL-2

μPD43256B-X

Recommended Soldering Conditions

Please consult with our sales offices for soldering conditions of the μ PD43256B-X.

Types of Surface Mount Device

μPD43256BGW-xxX-9JL : 28-pin PLASTIC TSOP(I) (8x13.4) (Normal bent) μPD43256BGW-xxX-9KL : 28-pin PLASTIC TSOP(I) (8x13.4) (Reverse bent) μPD43256BGW-AxxX-9JL : 28-pin PLASTIC TSOP(I) (8x13.4) (Normal bent) μPD43256BGW-AxxX-9KL : 28-pin PLASTIC TSOP(I) (8x13.4) (Reverse bent) μ PD43256BGW-BxxX-9JL : 28-pin PLASTIC TSOP(I) (8x13.4) (Normal bent) μPD43256BGW-BxxX-9KL : 28-pin PLASTIC TSOP(I) (8x13.4) (Reverse bent) μ PD43256BGW-xxX-9JL-A : 28-pin PLASTIC TSOP(I) (8x13.4) (Normal bent) μPD43256BGW-xxX-9KL-A : 28-pin PLASTIC TSOP(I) (8x13.4) (Reverse bent) μPD43256BGW-AxxX-9JL-A : 28-pin PLASTIC TSOP(I) (8x13.4) (Normal bent) μPD43256BGW-AxxX-9KL-A : 28-pin PLASTIC TSOP(I) (8x13.4) (Reverse bent) μPD43256BGW-BxxX-9JL-A : 28-pin PLASTIC TSOP(I) (8x13.4) (Normal bent) μPD43256BGW-BxxX-9KL-A : 28-pin PLASTIC TSOP(I) (8x13.4) (Reverse bent)

Revision History

Edition/	Pa	age Type of		Location	Description
Date	This	Previous	revision		(Previous edition $ ightarrow$ This edition)
	edition	edition			
6th edition/	p.1	p.1	Deletion	-	Description of Version X has been deleted.
Jun. 2006					

NOTES FOR CMOS DEVICES -

(1) VOLTAGE APPLICATION WAVEFORM AT INPUT PIN

Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between $V_{\rm IL}$ (MAX) and $V_{\rm IH}$ (MIN) due to noise, etc., the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between $V_{\rm IL}$ (MAX) and $V_{\rm IH}$ (MIN).

(2) HANDLING OF UNUSED INPUT PINS

Unconnected CMOS device inputs can be cause of malfunction. If an input pin is unconnected, it is possible that an internal input level may be generated due to noise, etc., causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND via a resistor if there is a possibility that it will be an output pin. All handling related to unused pins must be judged separately for each device and according to related specifications governing the device.

③ PRECAUTION AGAINST ESD

A strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it when it has occurred. Environmental control must be adequate. When it is dry, a humidifier should be used. It is recommended to avoid using insulators that easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors should be grounded. The operator should be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with mounted semiconductor devices.

(4) STATUS BEFORE INITIALIZATION

Power-on does not necessarily define the initial status of a MOS device. Immediately after the power source is turned ON, devices with reset functions have not yet been initialized. Hence, power-on does not guarantee output pin levels, I/O settings or contents of registers. A device is not initialized until the reset signal is received. A reset operation must be executed immediately after power-on for devices with reset functions.

(5) POWER ON/OFF SEQUENCE

In the case of a device that uses different power supplies for the internal operation and external interface, as a rule, switch on the external power supply after switching on the internal power supply. When switching the power supply off, as a rule, switch off the external power supply and then the internal power supply. Use of the reverse power on/off sequences may result in the application of an overvoltage to the internal elements of the device, causing malfunction and degradation of internal elements due to the passage of an abnormal current.

The correct power on/off sequence must be judged separately for each device and according to related specifications governing the device.

6 INPUT OF SIGNAL DURING POWER OFF STATE

Do not input signals or an I/O pull-up power supply while the device is not powered. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Input of signals during the power off state must be judged separately for each device and according to related specifications governing the device.

NEC μ PD43256B-X

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- "Special": Transportation equipment (automobiles, trains, ships, etc.), traffic control systems, anti-disaster systems, anti-crime systems, safety equipment and medical equipment (not specifically designed for life support).
- "Specific": Aircraft, aerospace equipment, submersible repeaters, nuclear reactor control systems, life support systems and medical equipment for life support, etc.

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